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1	L1	17734	densification or densif\$4	USPAT; EPO; JPO	2000/11/16 12:01
2	L5	2123	1 near15 (oxide or dielectric or insulat\$3)	USPAT; EPO; JPO	2000/11/16 12:02
3	L9	820	5 and (steam or wet or pyrogenic)	USPAT; EPO; JPO	2000/11/16 12:03
4	L13	124	5 same (steam or wet or pyrogenic)	USPAT; EPO; JPO	2000/11/16 12:41
5	L17	38	13 and (rapid or RTA or RTP or RTO)	USPAT; EPO; JPO	2000/11/16 12:37
6	L21	224	9 and (rapid or RTA or RTP or RTO)	USPAT; EPO; JPO	2000/11/16 12:40
7	L25	6967	(rapid adj thermal) or RTA or RTP or RTO	USPAT; EPO; JPO	2000/11/16 12:41
8	L29	426	25 same (steam or wet or pyrogenic)	USPAT; EPO; JPO	2000/11/16 12:42
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pyrogenic <near/5> oxidation

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